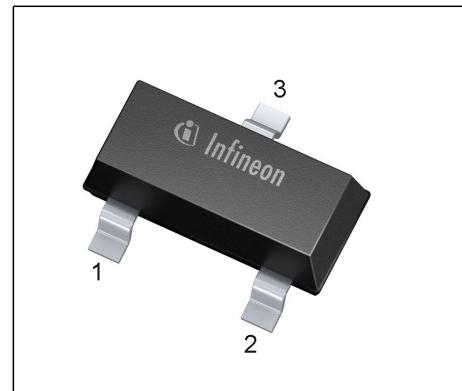


Low Noise Silicon Bipolar RF Transistor

- For low noise, high-gain amplifiers up to 2 GHz
- For linear broadband amplifiers
- $f_T = 8$ GHz, $NF_{min} = 1$ dB at 900 MHz
- Pb-free (RoHS compliant) package
- Qualification report according to AEC-Q101 available



ESD (Electrostatic discharge) sensitive device, observe handling precaution!

Type	Marking	Pin Configuration			Package
BFR193	RCs	1 = B	2 = E	3 = C	SOT23

Maximum Ratings at $T_A = 25$ °C, unless otherwise specified

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CEO}	12	V
Collector-emitter voltage	V_{CES}	20	
Collector-base voltage	V_{CBO}	20	
Emitter-base voltage	V_{EBO}	2	
Collector current	I_C	80	mA
Base current	I_B	10	
Total power dissipation ¹⁾ $T_S \leq 69$ °C	P_{tot}	580	mW
Junction temperature	T_J	150	°C
Storage temperature	T_{Stg}	-55 ... 150	

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ²⁾	R_{thJS}	140	K/W

¹ T_S is measured on the collector lead at the soldering point to the pcb

²For calculation of R_{thJS} please refer to Application Note AN077 (Thermal Resistance Calculation)

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

DC Characteristics

Collector-emitter breakdown voltage $I_C = 1 \text{ mA}, I_B = 0$	$V_{(\text{BR})\text{CEO}}$	12	-	-	V
Collector-emitter cutoff current $V_{CE} = 20 \text{ V}, V_{BE} = 0$	I_{CES}	-	-	100	μA
Collector-base cutoff current $V_{CB} = 10 \text{ V}, I_E = 0$	I_{CBO}	-	-	100	nA
Emitter-base cutoff current $V_{EB} = 1 \text{ V}, I_C = 0$	I_{EBO}	-	-	1	μA
DC current gain $I_C = 30 \text{ mA}, V_{CE} = 8 \text{ V}$, pulse measured	h_{FE}	70	100	140	-

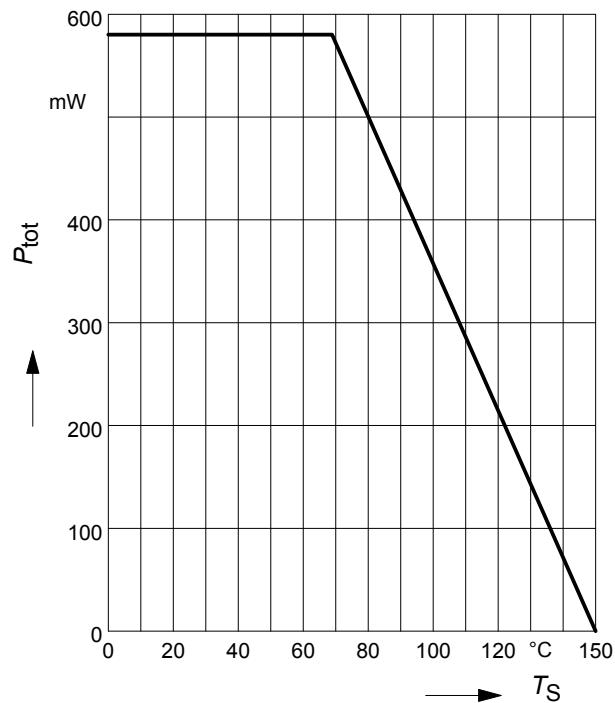
Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
AC Characteristics (verified by random sampling)					
Transition frequency $I_C = 50 \text{ mA}, V_{CE} = 8 \text{ V}, f = 500 \text{ MHz}$	f_T	6	8	-	GHz
Collector-base capacitance $V_{CB} = 10 \text{ V}, f = 1 \text{ MHz}, V_{BE} = 0, \text{ emitter grounded}$	C_{cb}	-	0.66	1	pF
Collector emitter capacitance $V_{CE} = 10 \text{ V}, f = 1 \text{ MHz}, V_{BE} = 0, \text{ base grounded}$	C_{ce}	-	0.28	-	
Emitter-base capacitance $V_{EB} = 0.5 \text{ V}, f = 1 \text{ MHz}, V_{CB} = 0, \text{ collector grounded}$	C_{eb}	-	2.25	-	
Minimum noise figure $I_C = 10 \text{ mA}, V_{CE} = 8 \text{ V}, Z_S = Z_{Sopt}, f = 900 \text{ MHz}$ $f = 1.8$	NF_{\min}	-	1	-	dB
-		-	1.6	-	
Power gain, maximum available ¹ $I_C = 30 \text{ mA}, V_{CE} = 8 \text{ V}, Z_S = Z_{Sopt}, Z_L = Z_{Lopt}, f = 900 \text{ MHz}$ $f = 1.8 \text{ GHz}$	G_{ma}	-	15	-	
-		-	10	-	
Transducer gain $I_C = 30 \text{ mA}, V_{CE} = 8 \text{ V}, Z_S = Z_L = 50\Omega, f = 900 \text{ MHz}$ $f = 1.8 \text{ GHz}$	$ S_{21e} ^2$	-	13	-	dB
-		-	7.5	-	
Third order intercept point at output ² $I_C = 30 \text{ mA}, V_{CE} = 8 \text{ V}, Z_S = Z_L = 50 \Omega, f = 0.9 \text{ GHz}$	IP_3	-	30	-	dBm
1dB Compression point $I_C = 30 \text{ mA}, V_{CE} = 8 \text{ V}, Z_S = Z_L = 50 \Omega, f = 0.9 \text{ GHz}$	$P_{-1\text{dB}}$	-	13	-	

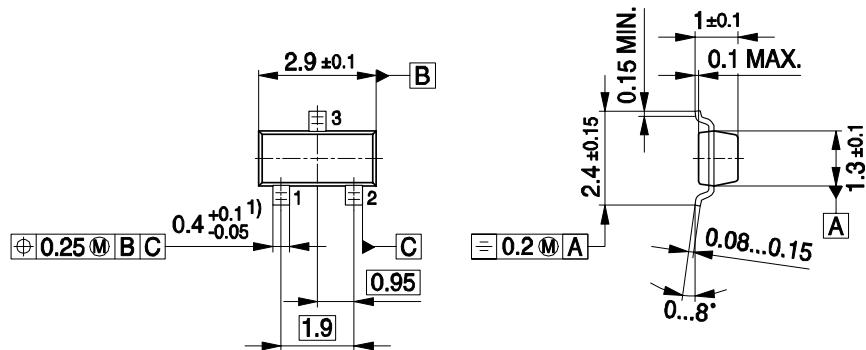
¹ $G_{ma} = |S_{21} / S_{12}| (k - (k^2 - 1)^{1/2})$
²IP3 value depends on termination of all intermodulation frequency components.

Termination used for this measurement is 50Ω from 0.2 MHz to 12 GHz

Total power dissipation $P_{\text{tot}} = f(T_S)$



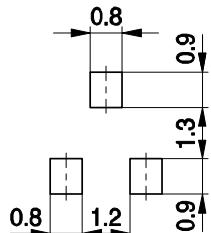
Package Outline



1) Lead width can be 0.6 max. in dambar area

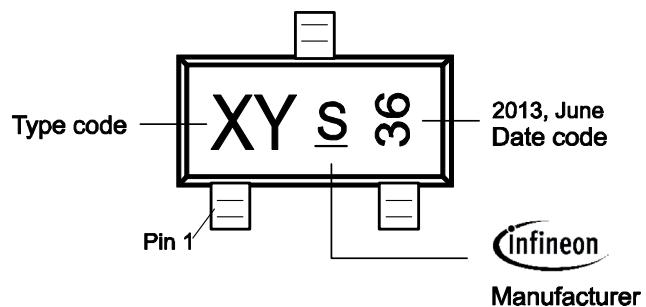
SOT23-PO V08

Foot Print



SOT23-FPR V08

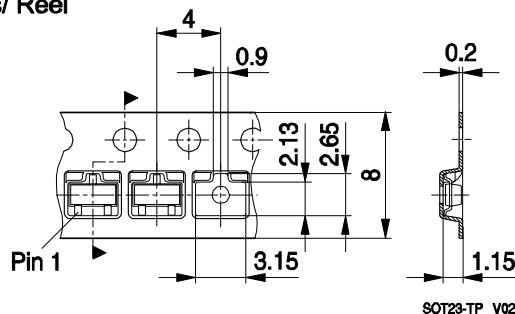
Marking Layout (Example)



Standard Packing

Reel Ø 180 mm = 3.000 Pieces/ Reel

Reel Ø 330 mm = 10.000 Pieces/ Reel



SOT23-TP V02

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